

#9/ Amot  
A  
3/28/02  
✓

PATENT  
Customer No. 22,852  
Attorney Docket No. 04329.2222



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Kouji MATSUO, et al. ) Group Art Unit: 2814  
)  
Serial No.: 09/492,780 ) Examiner: Rao, Steven H.  
)  
Filed: January 28, 2000 )  
)  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF MANUFACTURING )  
THE SAME )

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Office Action dated October 19, 2001, with a period for response extending through April 14, 2002 by the granting of the Petition to Restart Period for Response to Office Action on March 5, 2002, please amend the application as follows:

IN THE CLAIMS:

Please amend claims 12 and 16 – 18 as follows:

12. (Amended) A semiconductor device, comprising:

a semiconductor substrate;

a metal-containing insulating film formed directly or indirectly on said semiconductor substrate, said metal-containing insulating film including a plurality of first insulating regions each of which is formed of a grain containing a metal oxide and a second insulating region

RECEIVED  
MAR 20 2002  
TC 2800 MAIL ROOM

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com